

-4-

Docket No. 740756-2205
Application Serial No. 09/651,889REMARKS

The Office Action of November 4, 2002 was received and reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application.

Claims 1-3 and 10-17 are pending in the present application. By this amendment, claims 1-3, and 11-16 have been amended.

Referring to the detailed Office Action, claims 1-3, and 11-16 stand rejected under 35 U.S.C. §102(b) as anticipated by previously cited Japanese Patent 404152676 (hereafter JP '676). Further, claims 10 and 17 stand rejected under 35 U.S.C. §103(a) as unpatentable over JP '676, and further in view of Japanese Patent No. 2001028338 (hereafter JP '338). In view of the actions above and the remarks below, reconsideration and withdrawal of the pending rejections are respectfully requested.

In the rejection, the Examiner asserted that JP '676 discloses an active layer having convex and concave portions in a channel forming region. However, in JP '676, the channel forming region 1-7 itself appears to be entirely concaved in the a film thickness direction. Further, since Fig. 1(j) of JP '676 is a cross-sectional view along the channel length direction, the structure along the channel width cannot be observed.

In order to further clarify the structure of the present invention, the claims have been amended, as shown above, to recite that a portion of the channel-forming region is convexed or concaved in the channel width direction.

In order to illustrate the argument presented above, Applicants have prepared an attachment submitted herewith, which indicates a channel length direction, a channel width direction, and a film thickness direction by referring to Fig. 1 of the present invention and Fig. 1(j) of JP '676.

Consequently, since each and every feature of the present claims is not taught (and is not inherent) in the teachings of JP '676, as is required by MPEP Chapter 2131 in order to establish

-5-

Docket No. 740756-2205
Application Serial No. 09/651,889

anticipation, the rejection of claims 1-3, and 11-16, under 35 U.S.C. § 102(b), as anticipated by JP '676 would be improper.

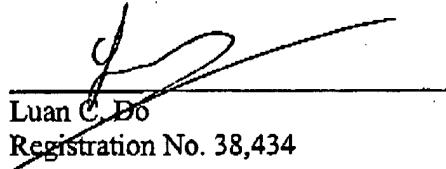
As JP '676 is deficient, as discussed above, its combination with JP '338 in the §103(a) rejection of claims 10 and 17 would also be improper.

In view of the amendments and arguments set forth above, Applicants respectfully request reconsideration of all the pending rejections.

CONCLUSION

Having responded to the rejection set forth in the outstanding Office Action, it is submitted that claims 1-3 and 10-17 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited. In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicant's undersigned representative.

Respectfully submitted,


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-6-

Docket No. 740756-2205
Application Serial No. 09/651,889MARKED-UP VERSION OF AMENDED CLAIMS

1. (Thrice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,
wherein a portion of the channel forming region [has a convex portion or a concave portion extending] is convexed or concaved in a channel width direction.

2. (Thrice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,
wherein a portion of the channel forming region [has a convex portion or a concave portion extending] is convexed or concaved in a channel width direction,
wherein zero or one grain boundary is contained in the channel forming region.

3. (Thrice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,
wherein a portion of the channel forming region [has a convex portion or a concave portion extending] is convexed or concaved in a channel width direction,
wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

11. (Twice Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein a portion of said channel forming region [has at least one convex portion extending] is convexed in a direction perpendicular to a channel length direction.

12. (Twice Amended) A semiconductor device comprising:

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-7-

Docket No. 740756-2205
Application Serial No. 09/651,889

a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region [has at least one concave portion extending] is concaved in a direction perpendicular to a channel length direction.

13. (Twice Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region [has at least one convex portion extending] is convexed in a channel width direction.

14. (Twice Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region [has at least one concave portion extending] is concaved in a channel width direction.

15. (Twice Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,

wherein a portion of said channel forming region [has at least one convex portion extending] is convexed in a direction perpendicular to a carrier flow direction.

16. (Twice Amended) A semiconductor device comprising:

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-8-

Docket No. 740756-2205
Application Serial No. 09/651,889

a semiconductor layer formed over a substrate;
a channel forming region and source and drain regions formed in said semiconductor layer; and
wherein a portion of said channel forming region [has at least one concave portion extending] is concaved in a direction perpendicular to a carrier flow direction.

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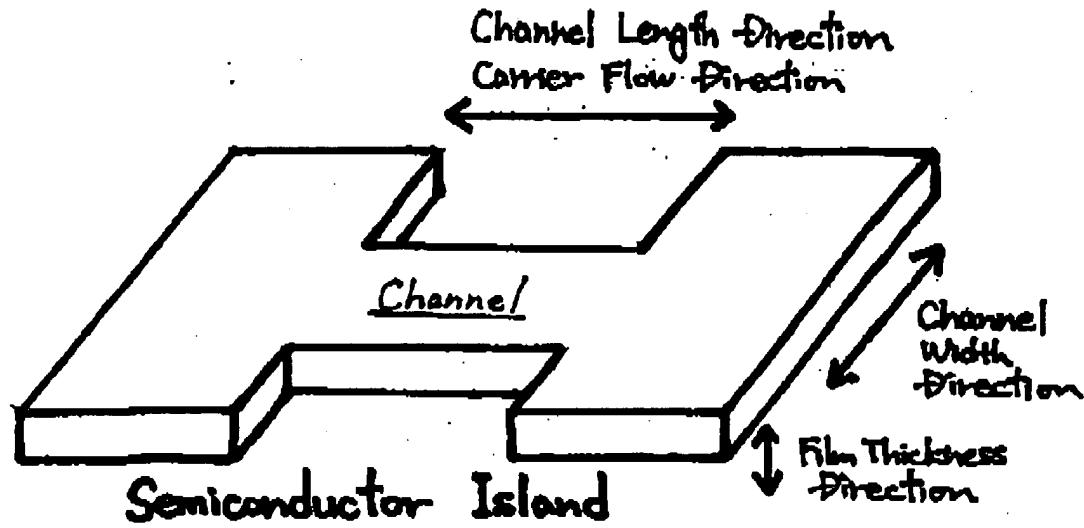
ATTACHMENT

Fig. 1C of
the present invention
(Plane View)

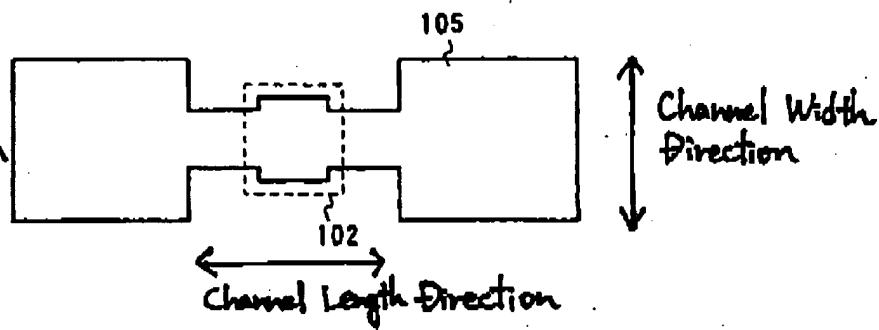


Fig. 1(j) of
JP 4-152676
(Cross-Sectional View)

